



SS210LB

2.0 AMP SCHOTTKY BARRIER RECTIFIERS



FEATURES

- * Ideal for surface mount applications
- * Easy pick and place
- * Built-in strain relief
- * Low forward voltage drop

MECHANICAL DATA

- * Case: Molded plastic
- * Epoxy: UL 94V-0 rate flame retardant
- * Metallurgically bonded construction
- * Polarity: Color band denotes cathode end
- * Mounting position: Any
- * Weight: 0.093 grams

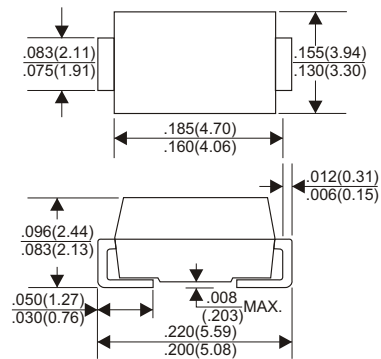
VOLTAGE RANGE

100 Volts

CURRENT

2.0 Ampere

DO-214AA(SMB)



Dimensions in inches and (millimeters)

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25 °C ambient temperature unless otherwise specified.
Single phase half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

TYPE NUMBER	SS210LB	UNITS
Maximum Recurrent Peak Reverse Voltage	100	V
Maximum RMS Voltage	70	V
Maximum DC Blocking Voltage	100	V
Maximum Average Forward Rectified Current		
See Fig. 1	2.0	A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	50	A
Maximum Instantaneous Forward Voltage at 2.0A	0.67	V
Maximum DC Reverse Current Ta=25 °C	0.1	mA
at Rated DC Blocking Voltage Ta=125 °C	20	mA
Typical Junction Capacitance (Note1)	50	pF
Typical Thermal Resistance R JA (Note 2)	70	°C/W
Operating Temperature Range Tj	-55 to +150	°C
Storage Temperature Range Tstg	-55 to +150	°C

NOTES:

1. Measured at 1MHz and applied reverse voltage of 4.0V D.C.
2. P.C.B. mounted with 0.2" x 0.2" (5.0 mm x 5.0 mm) copper pad areas

RATING AND VCHARACTERISTIC CURVES(SS210LB)

FIG.1-FORWARD CURRENT DERATING CURVE

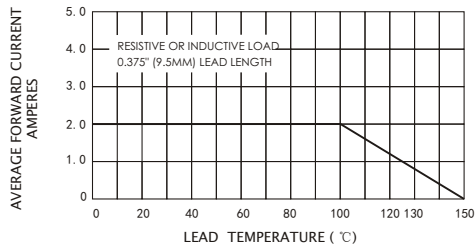


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

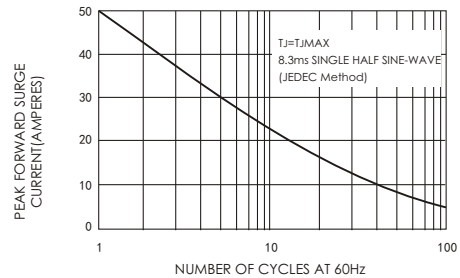


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

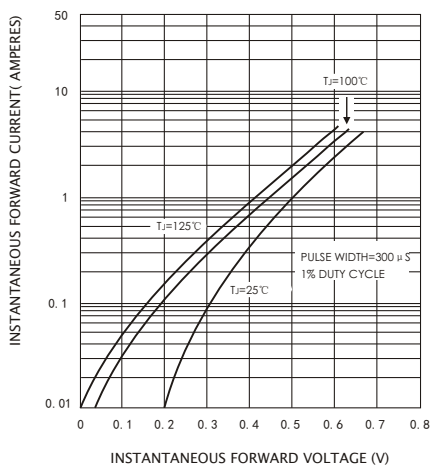


FIG.4-TYPICAL REVERSE CHARACTERISTICS

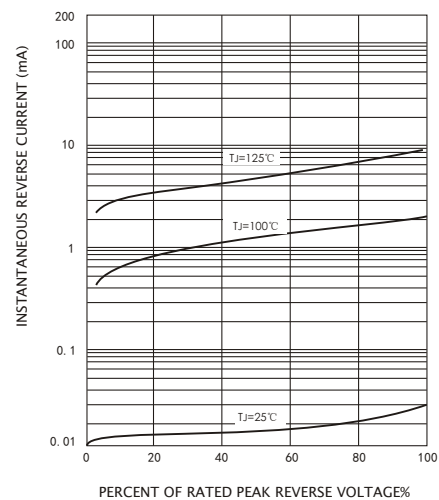
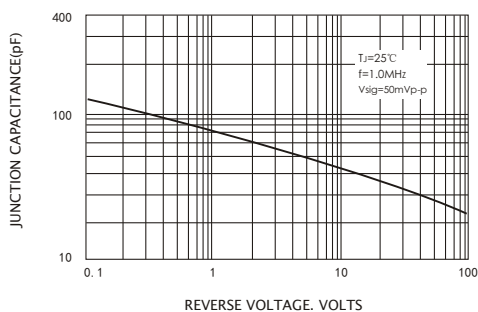


FIG.5-TYPICAL JUNCTION CAPACITANCE



Attention:

The graph is for reference only, can't be the basis for judgment.

Any and all information described or contained herein are subject to change without notice due to product/technology improvement.